

1-Line Bi-directional 2.5V ESD Protection Diode

Description

The PESDU2581P1 is a 2.5V bi-directional ESD protection diode, to provide fast response time and ultra low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data line. The PESDU2581P1 complies with the IEC 61000-4 -2 (ESD) standard with ±30kV air and ± 30kV contact discharge. It is assembled into an ultra-small 1.0x0.6x 0.5mm DFN lead-free package. The small size and high ESD surge protection make PESDU2581P1 an ideal choice to protect cellphone, digital cameras, audio players and many other portable applications.

Features

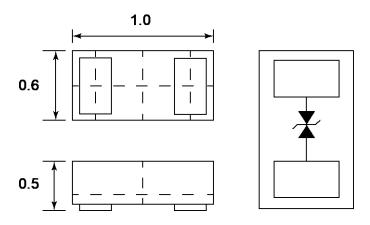
- Protects one data line
- Ultra low leakage: nA level
- Ultra low operating voltage: 2.5V
- Ultra low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test

Air discharge: ±30kV

Contact discharge: ±30kV

- IEC61000-4-5 (Lightning) 28A (8/20µs)
- RoHS Compliant

Dimensions and Pin Configuration



Package Dimensions

Circuit and Pin Schematic

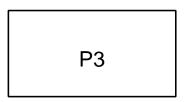
Mechanical Characteristics

- Package: DFN1006-2 (1.0×0.6×0.5mm)
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets & Accessories
- Personal Digital Assistants (PDAs)
- Notebooks & Handhelds
- Portable Instrumentation
- Digital Cameras

Marking Information



P3 = Device Marking Code

Ordering Information

Part Number	Shipping	Reel Size
PESDU2581P1	10000/Tape & Reel	7 inch



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

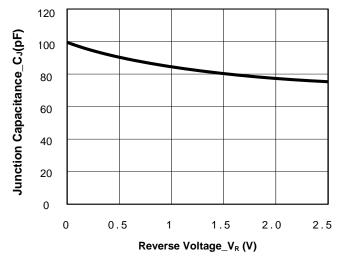
Parameter	Symbol Value		Unit		
Peak Pulse Power (8/20µs)	Ppk 308		W		
Peak Pulse Current (8/20µs)	l _{PP}	I _{PP} 28			
ESD per IEC 61000-4-2 (Air)	V	±30	12/		
ESD per IEC 61000-4-2 (Contact)	Vesd	±30	- kV		
Lead temperature	TL	260	°C		
Operating Temperature Range	Тор	-40 ~ + 85	Ĉ		
Storage Temperature Range	T _{STG}	−55 ~ + 150	°C		

Electrical Characteristics (T_A=25°C unless otherwise specified)

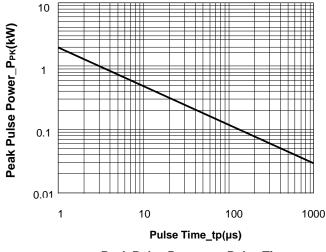
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			2.5	V	
Reverse Breakdown Voltage	V_{BR}	3.3				I _T = 1mA
Reverse Leakage Current	I _R			0.2	μA	V _{RWM} = 2.5V
Clamping Voltage	Vc			5	V	I _{PP} = 1A (8/20µs pulse)
Clamping Voltage	Vc			11	V	I _{PP} = 28A (8/20µs pulse)
Junction Capacitance	Сл			100	pF	V _R = 0V, f = 1MHz



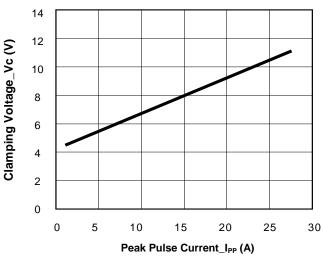
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



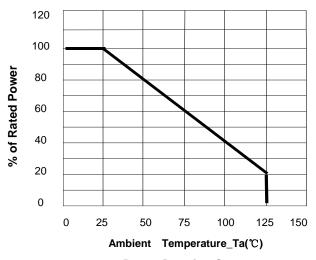
Junction Capacitance vs. Reverse Voltage



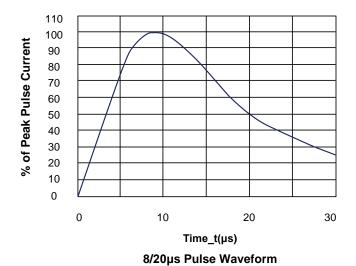
Peak Pulse Power vs. Pulse Time



Clamping Voltage vs. Peak Pulse Current

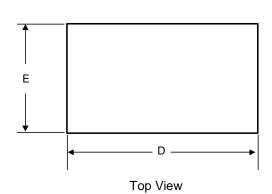


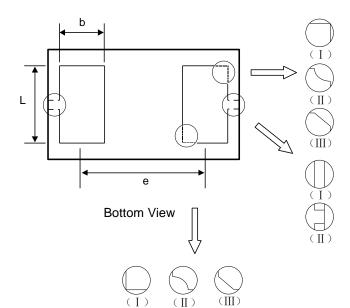
Power Derating Curve

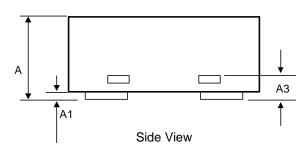




DFN1006-2 Package Outline Drawing

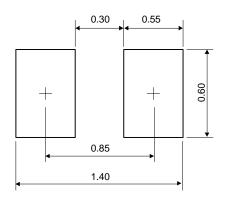






Symbol	Dimensions in Millimeters			
	Min.	Тур.	Max.	
А	0.340	0.450	0.530	
A1	0.000	0.020	0.050	
А3	0.125 Ref.			
D	0.950	1.000	1.075	
E	0.490	0.600	0.675	
b	0.200	0.250	0.300	
L	0.450	0.500	0.550	
e	0.650 BSC			

Recommended PCB Layout (Unit: mm)



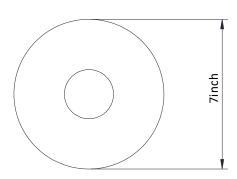
Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

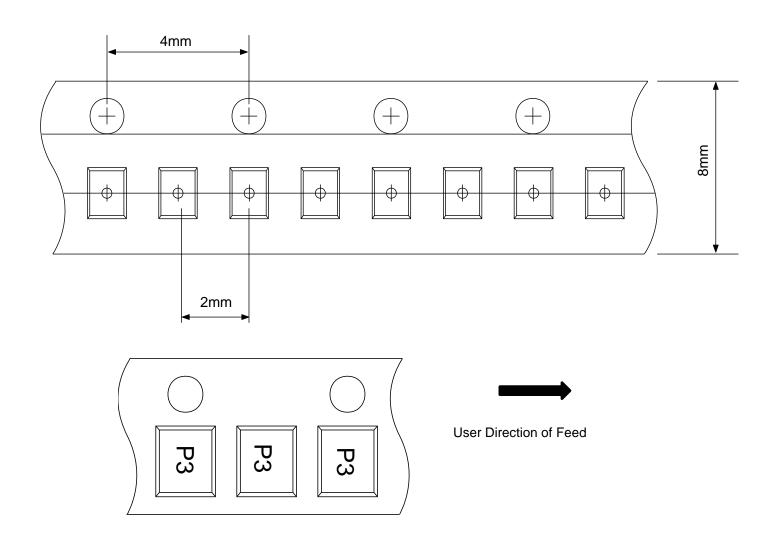


TAPE AND REEL INFORMATION





Tape Dimensions





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